

FIG. 1a
(Prior art)

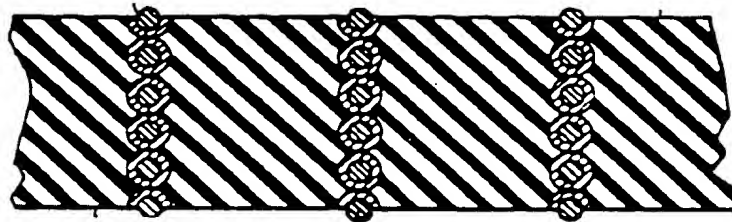


FIG. 1b
(Plasma etched)

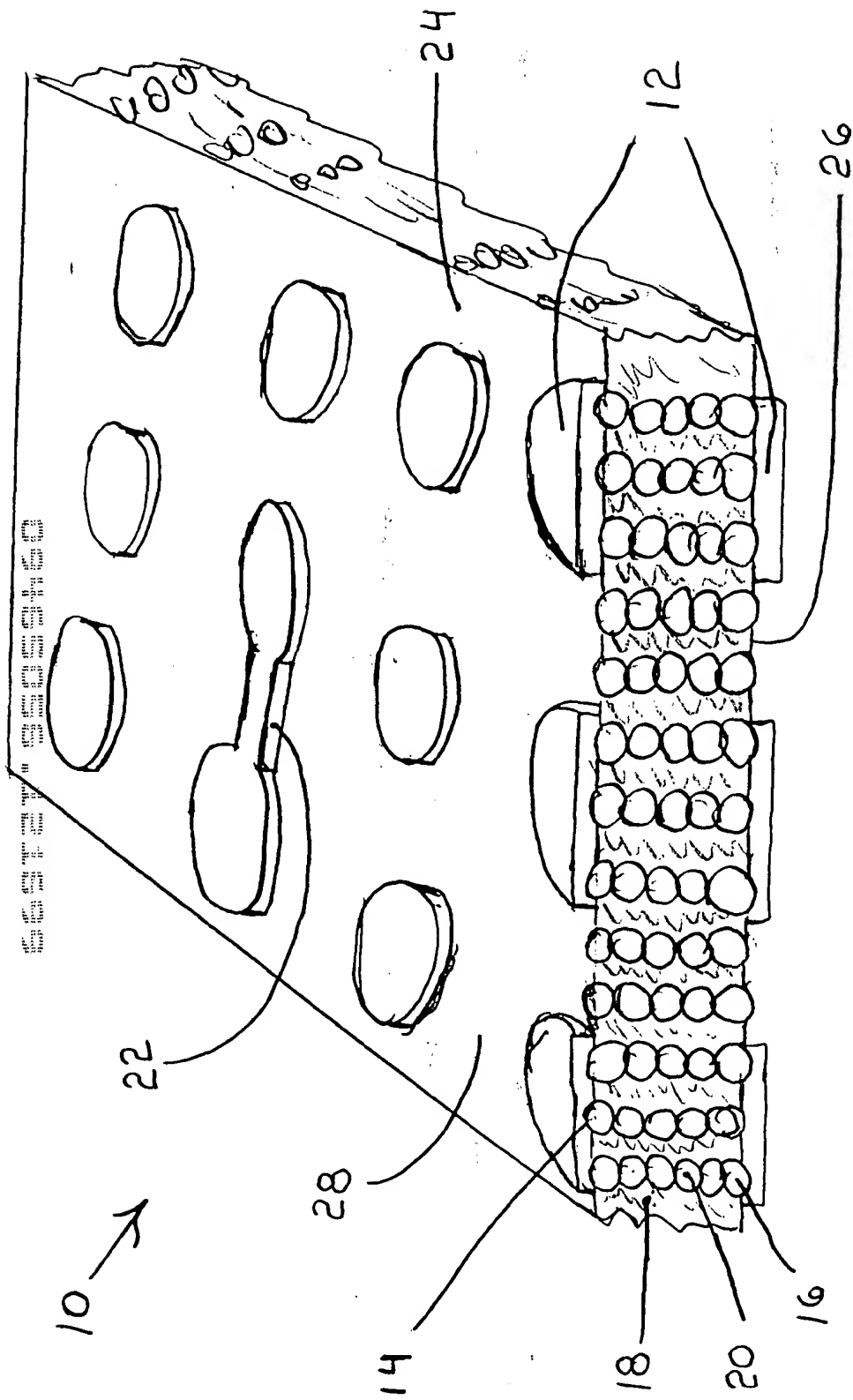


FIG. 2

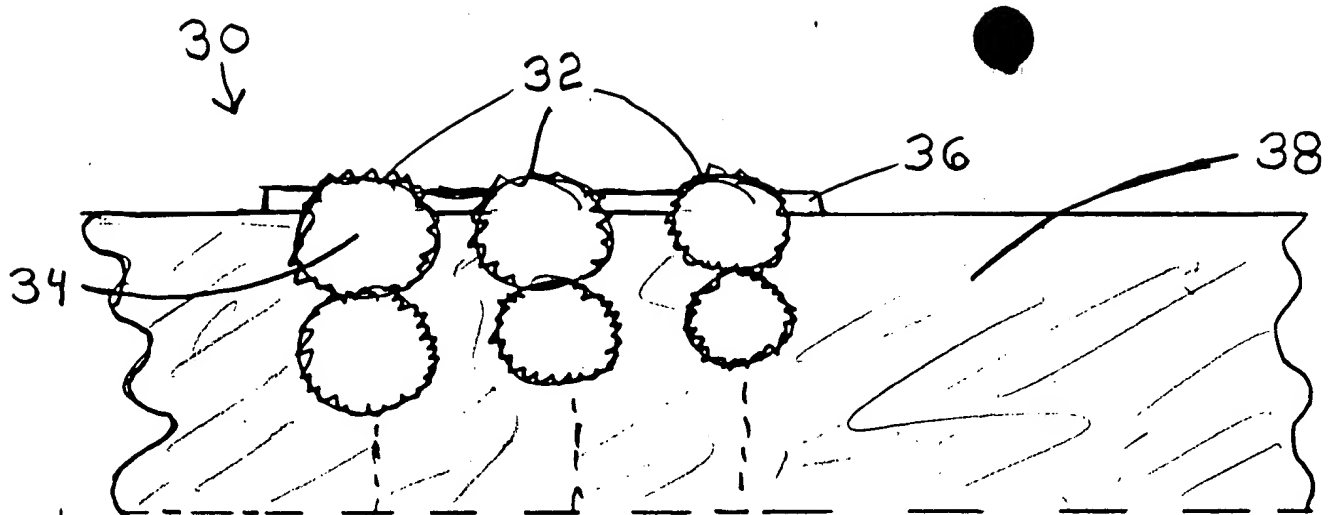


FIG. 3

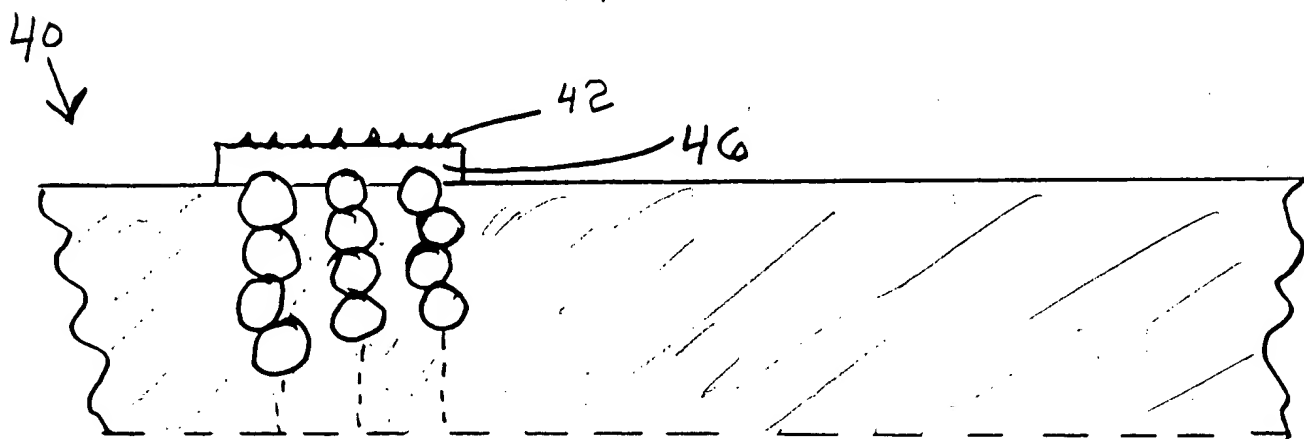


FIG. 4

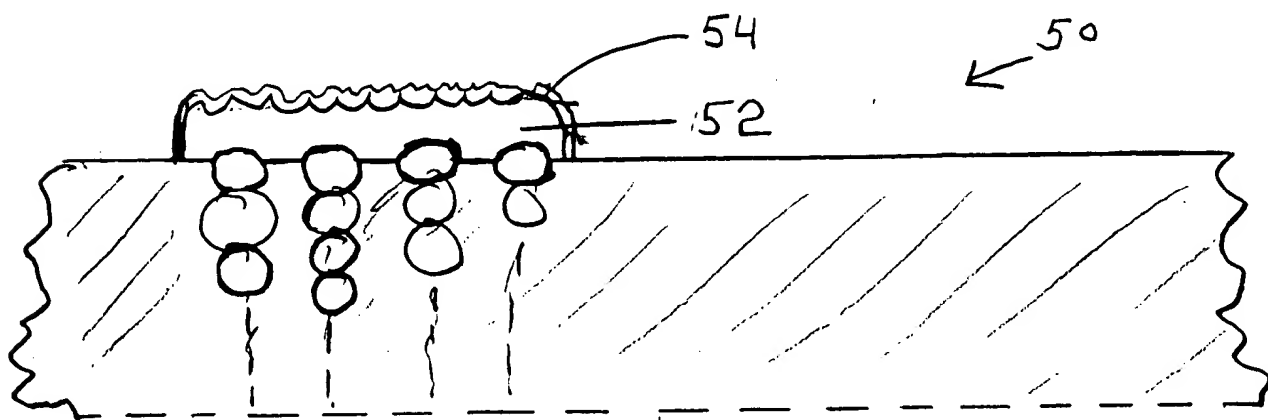
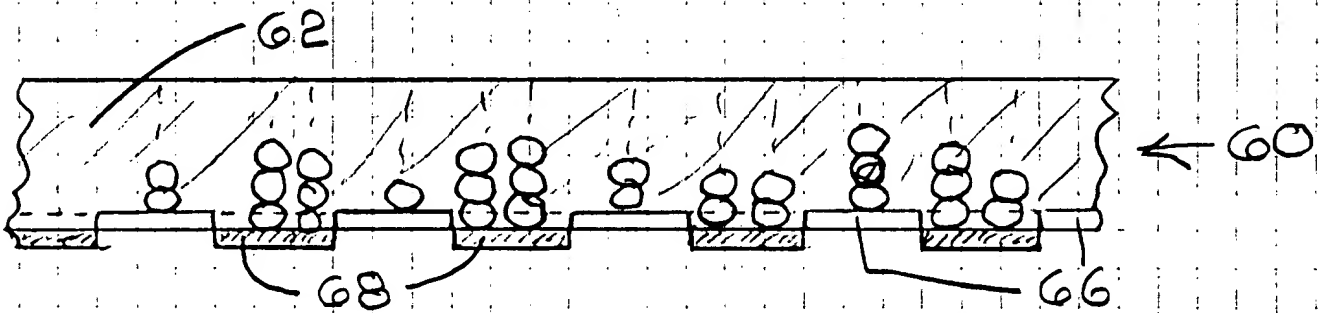
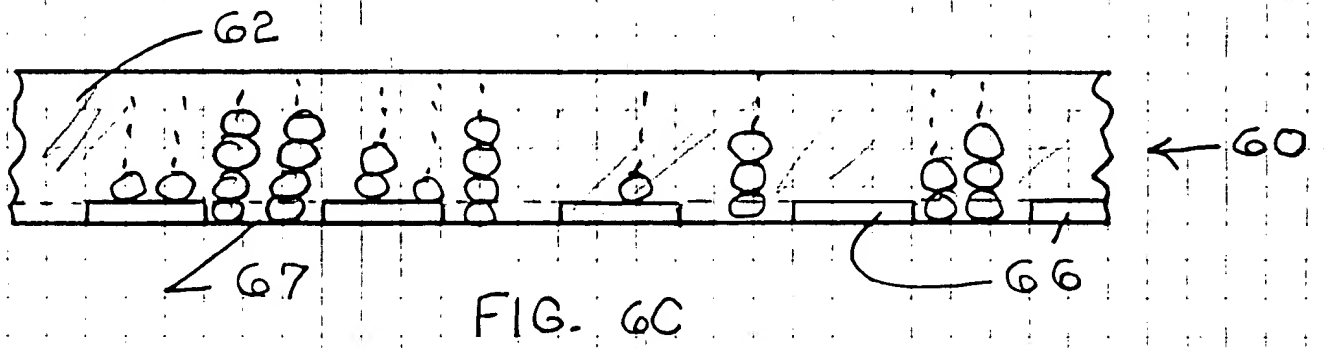
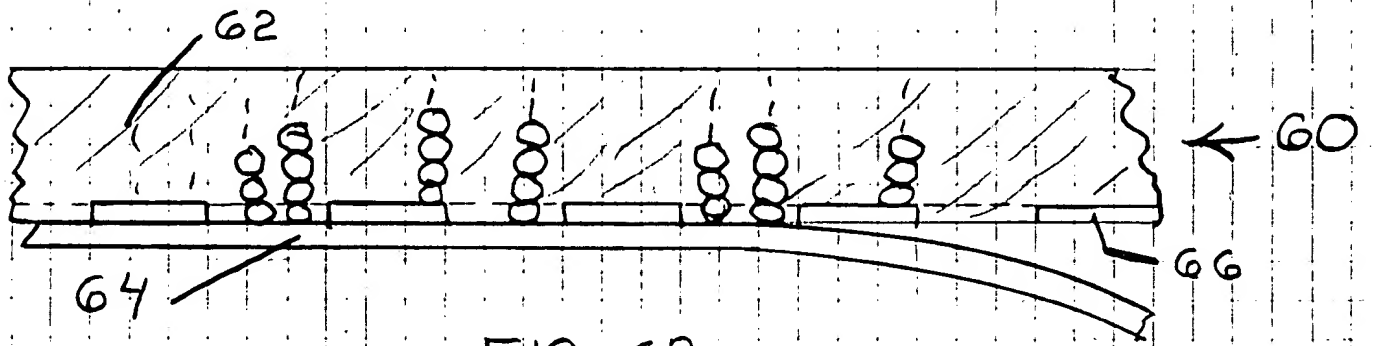
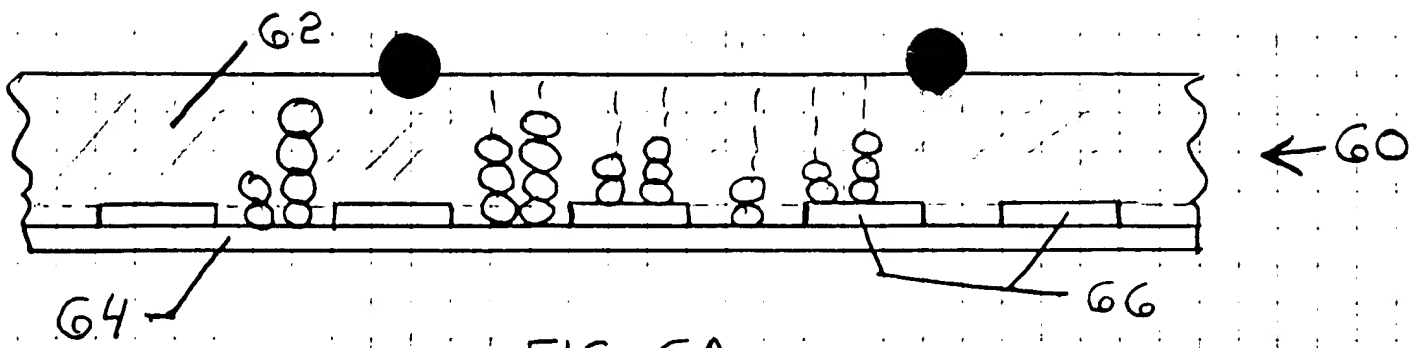


FIG. 5



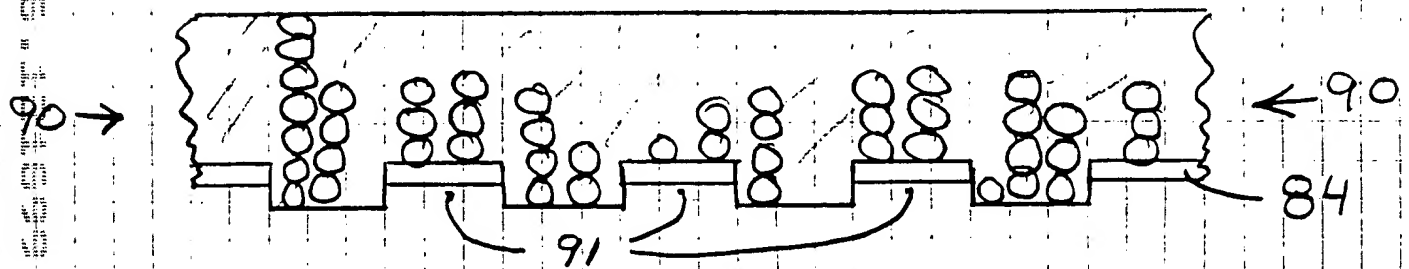
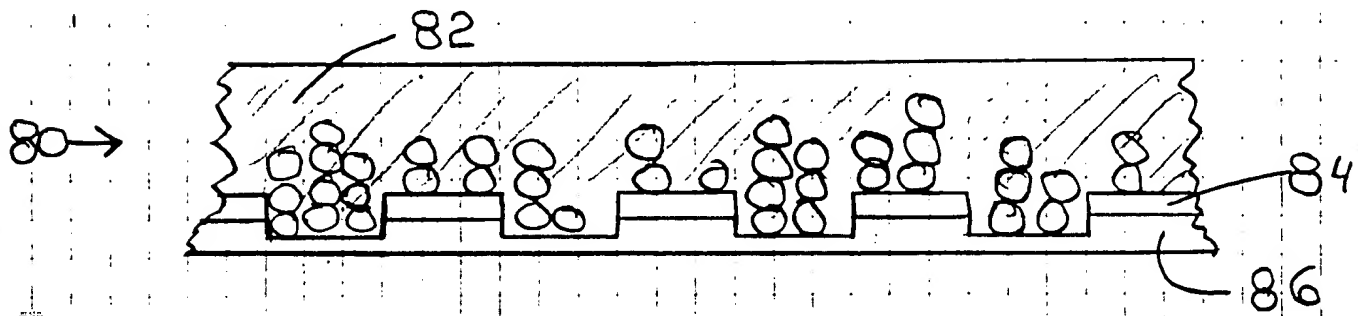
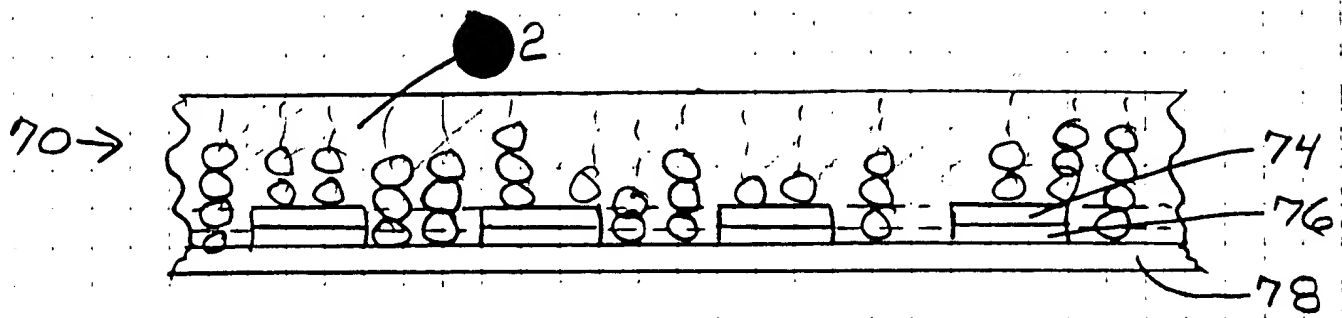


FIG. 10 is a cross-sectional view of a device 100 in a first state. The device 100 includes a substrate 102, a layer 104, and a layer 106. A plurality of elements 80 are disposed on the substrate 102. Each element 80 includes a first part 82 and a second part 84. The first part 82 is disposed on the substrate 102, and the second part 84 is disposed on the layer 104. The layer 106 is disposed on the layer 104. The device 100 is shown in a first state, where the elements 80 are in a first position.

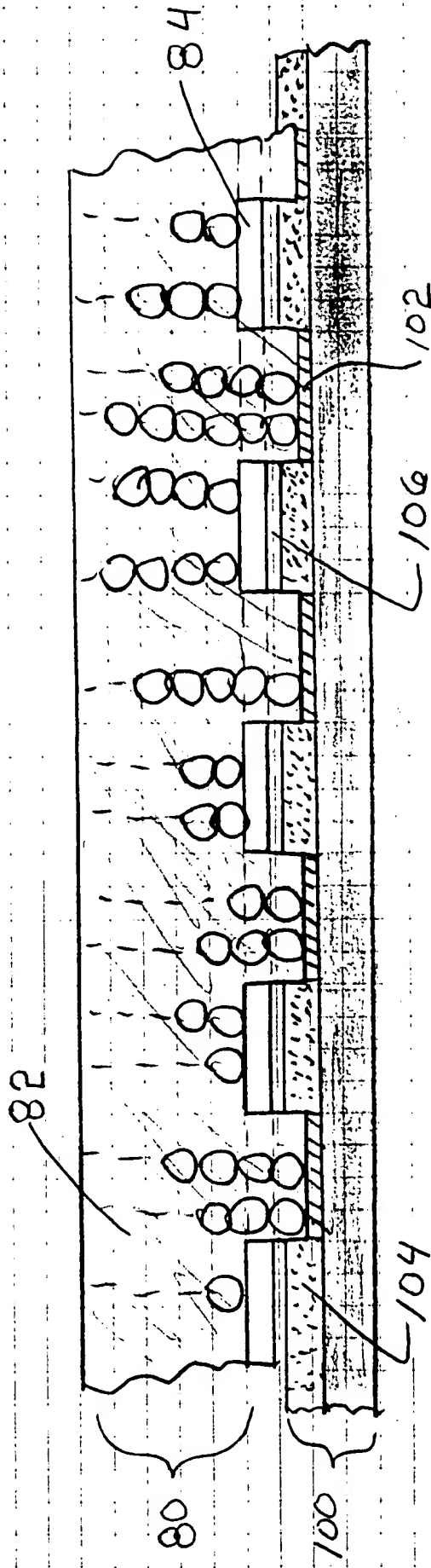


FIG. 10

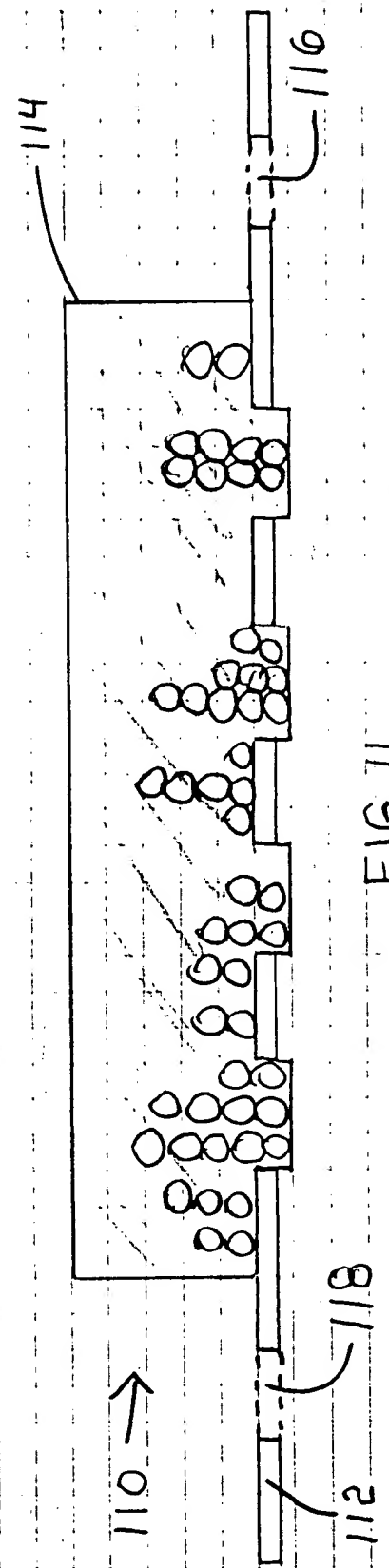
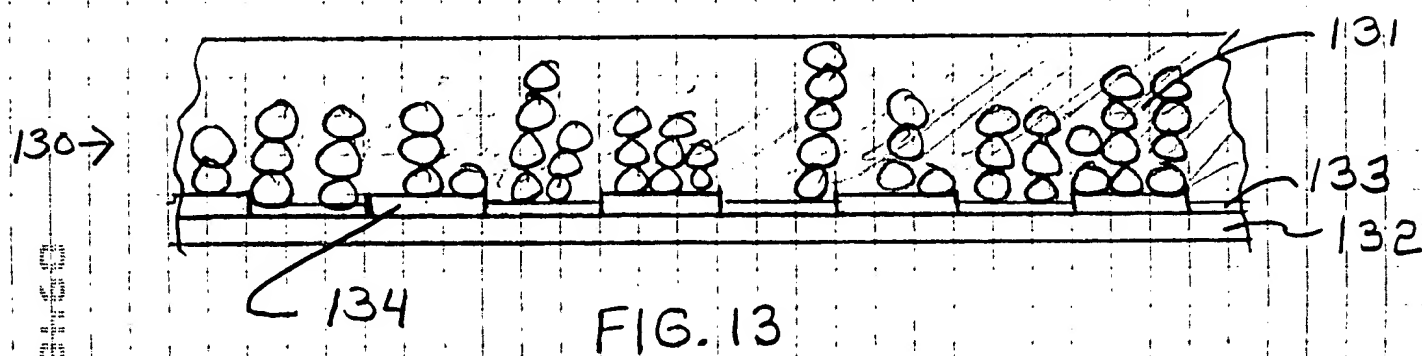
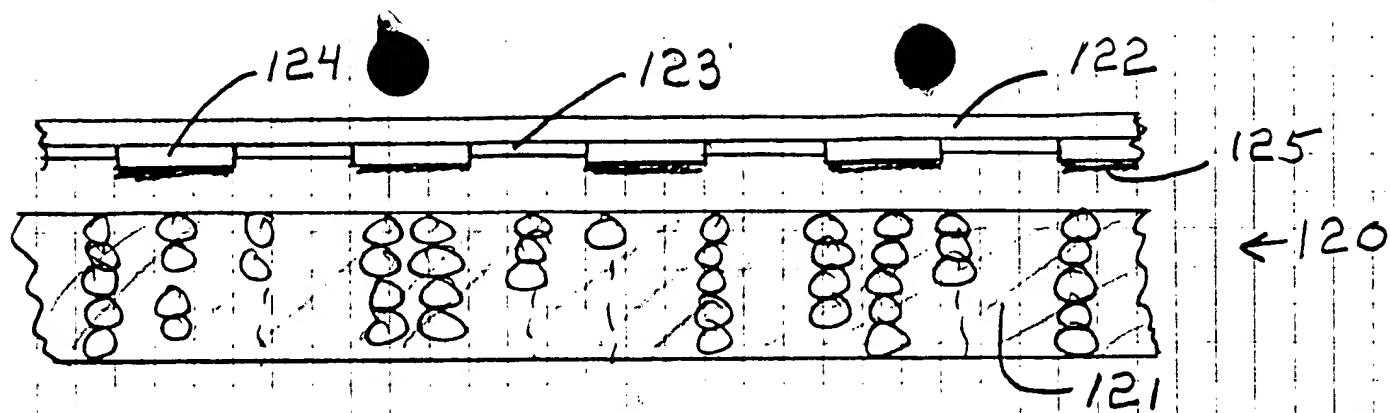


FIG. 11



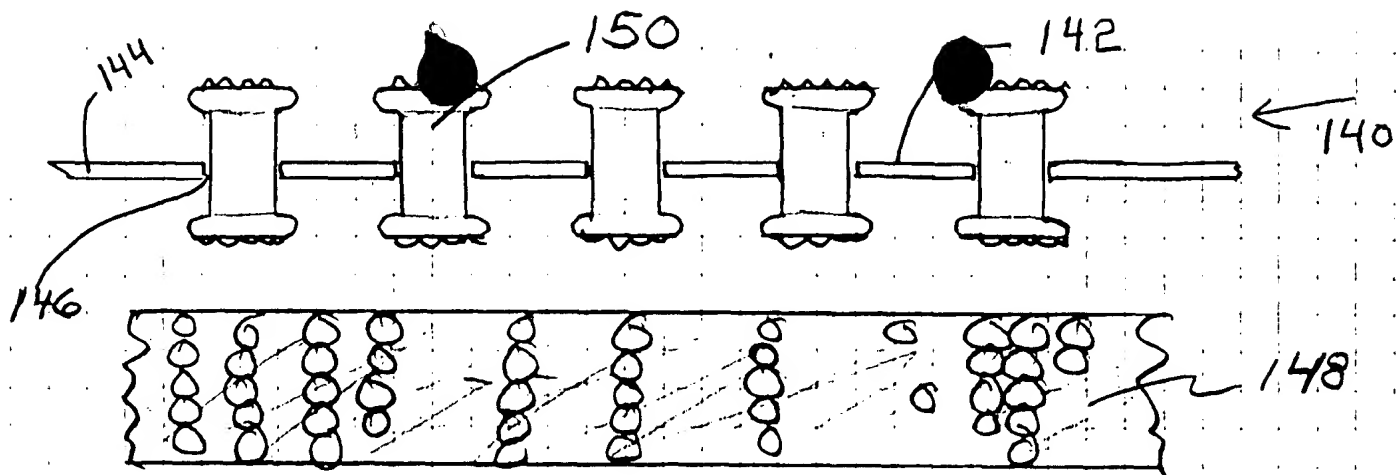


FIG. 14

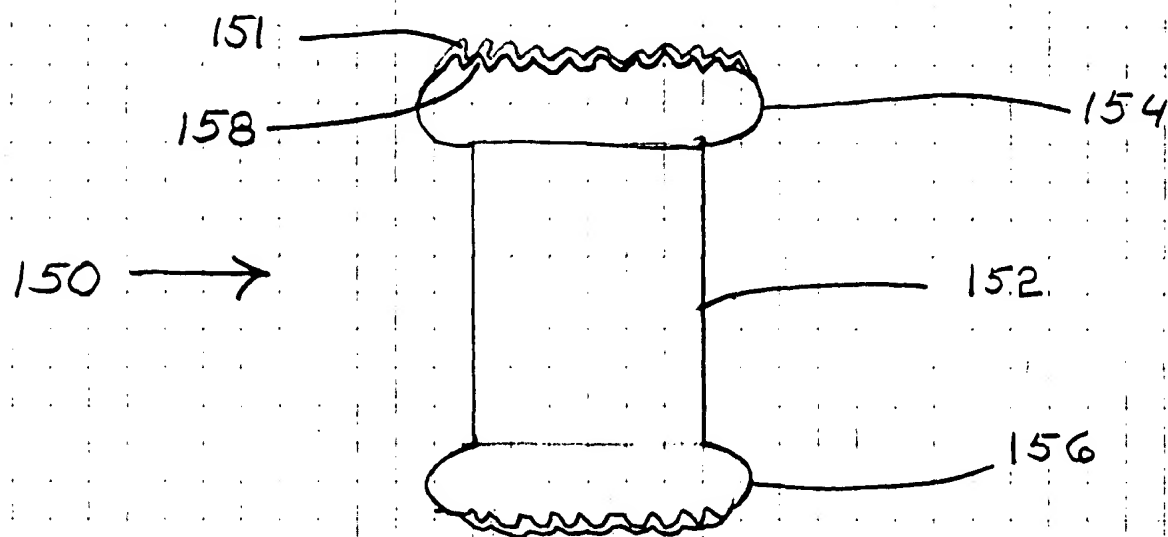


FIG. 15

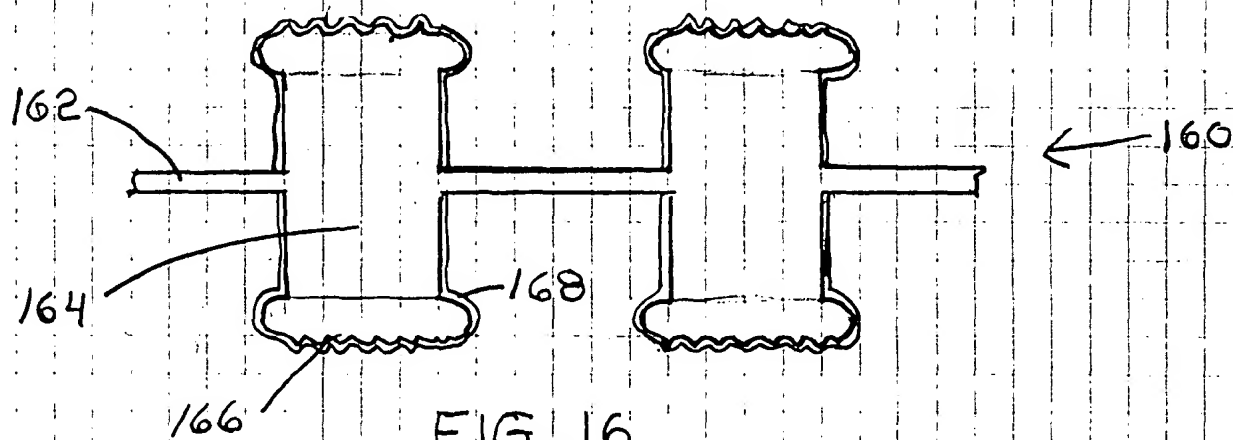


FIG. 16

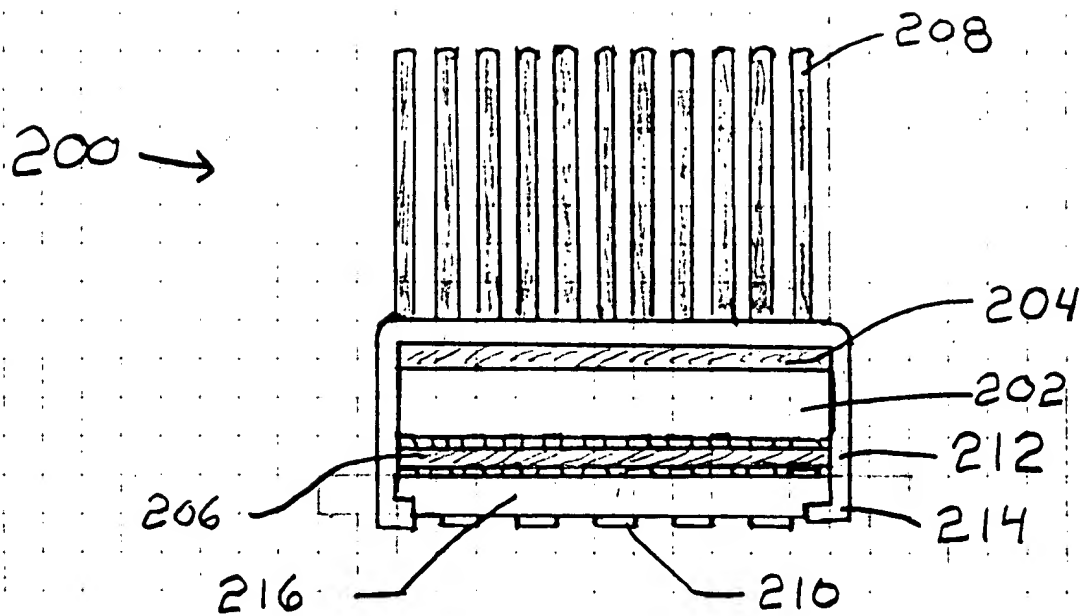


FIG. 17